Effects of metal-free conjugated oligomer as a surface modifier in hybrid polymer/ZnO solar cells

Chiang-Ting Chen a, Fang-Chi Hsu b,*, Yun-Ming Sung a, Hsueh-Chung Liao c, Wei-Che Yen c, Wei-Fang Su c, Yang-Fang Chen a, n

a Department of Physics, National Taiwan University, Taipei 106, Taiwan
b Department of Materials Science and Engineering, National United University, Miaoli 360, Taiwan
c Department of Materials Science and Engineering, National Taiwan University, Taipei 106, Taiwan

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Abstract

The interface property has been one of the critical issues in developing hybrid polymer/metal oxide solar cells. We synthesize a conjugated oligomer, an amine- and bromine-terminated 3-hexyl thiophene (O3HT-(Br)NH2), to modify the ZnO-nanorod (ZnO-NR) surface in hybrid polymer/ZnO-NR photovoltaic cells. This oligomer is of the same repeat unit structure as and /C24 1/12 the contour length of that of the light-harvesting polymer. In addition to passivate the NR surface, the presence of this conjugated oligomer enhances the electron mobility, and drives larger hole density toward the anodic surface for collection. The improved charge transport property of the hybrid is presumably a result of modulating the nanomorphology of the bi-carrier transport network induced by the conjugated oligomer. As a result, there is a large enhancement in photocurrent and photovoltage leading to an improved device performance of /C24 35%.

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1. Introduction

Polymer based solar cells (PSCs) have received considerable attentions by scientists for the past decade because of being considered as a promising alternative for low-cost energy device production [1–5]. A typical approach used to integrate polymer materials in PSC is to employ the bulk heterojunction (BHJ) concept [6–10], in which the donor and acceptor materials are closely intermixed in a nanometer scale. In the BHJ structure, there is a large interfacial area created beneficial for exciton dissociation; however, the resulting interpenetration charge transport network formed by donor and acceptor phases is bi-continuous. Under such a condition, electron (hole) traveling pathway is indirect and uncontrollable, and this morphological nature could be detrimental to the carrier mobility as compared to the system of ordered transport paths. One of the methods to integrate the advantages of a large exciton dissociation surface and direct charge transport pathways is to introduce ordered nanostructures into the BHJ system.

ZnO is an environmental friendly and low-cost semiconducting material with good air stability; especially, it is highly processable using low temperature solution-phase growth method [11,12] or printing/coating techniques on a range of substrates [13–16]. Successful use of ZnO nanostructures such as in the form of nanorods [17–22] and nano-ridges [23] as an electron transporter have been demonstrated. Those nanostructured ZnO patterns not only offer controllable transport path to direct electrons to reach the cathode but also serve as a hole blocker simultaneously. A power conversion efficiency (PCE) of PSC based on ZnO-nanorod (ZnO-NR) arrays arrays in the most prominent photoactive system, poly(3-hexythiophene):(6,6)-phenyl C61 butyric acid methyl ester (P3HT:PCBM), has improved from 2.03% [18] to 3.56% [19] after including an anodic hole transport layer to modify the polymer/metal interface.

From the material perspective, the inorganic ZnO-NR/polymer interface is also problematic due to the different surface characters. The semiconducting ZnO-NRs tend to be hydrophilic while polymers are hydrophobic. Thus, it is essential and critical to manipulate the ZnO-NR surface character in order to obtain a good electrical coupling between these two classes of materials. A few research groups have intended to improve the ZnO-NR surface property for a better compatibility with organics based on various influences. Mercurochrome (C20H8Br2HgNa2O) [24] and N719 dye [25] were used to enhance the interfacial charge transport; anilinethiols were employed to modulate the crystalline order of the polymer [26]; mixing molecules of octyltrimethoxysilane and aminopropyltrimethoxysilane were selected to...
control the surface energy of the ZnO film for a rich photoactive layer morphology [27]. Though these surface modifiers function differently, the ultimate goal is to improve the performance of the solar cells. Unfortunately, these reported surface modifiers are either unfriendly to the environment or insulating against charge transport.

In this paper, we synthesize a relatively lower-cost and metal-free conductive molecule, an amine- and bromine-terminated 3-hexyl thiophene oligomer (oligo-3HT-(Br)NH$_2$, O3HT-NH$_2$) to adsorb on the ZnO-NR surface in an inverted hybrid ITO/ZnO-NR/ P3HT:PCBM/Ag solar cell configuration. Our chosen oligomer is specially designed to have dual functions. The amino terminated functional group of the oligomer provides good affinity toward ZnO. At the same time, the oligomer contains approximately 20 repeating units having the same chemical structure as the light-harvesting conducting polymer, P3HT, which gives better interfacial compatibility between polymer blend and ZnO-NRs. This conjugated O3HT-NH$_2$ oligomer is able to passivate the ZnO-NR surface and prevent the back transfer of electrons for its large spatial dimension. Additionally, in the presence of the O3HT-NH$_2$ molecule, the electron mobility of the hybrid increases while higher hole concentration reaches the anodic surface for collection. The result indicates a modulation of microscopic morphology of bi-carrier transport pathways toward a more ordered and efficient configuration. Hence, the power conversion efficiency of the modified photovoltaic cell enhances as a result of improved photocurrent and photovoltage.

2. Experimental details

The chemical structure of oligo-3HT-(Br)NH$_2$ is shown in Fig. 1(a). The oligo-3HT-(Br)NH$_2$ (Mw = 3,438 KDa, PDI = 3.21) was synthesized by Grignard reaction [28,29], a kind of living polymerization. The molecular weight of the oligomer was controlled by the molar ratio of monomer to Ni catalyst in the feed. Briefly, in a three-neck round bottom flask, monomer: 2,5-dibromo-3-hexylthiophene 1 (3.26 g, 10.0 mmol) was dissolved in tetrahydrofuran (THF) (200 mL) and stirred under N$_2$. 2,5-dibromo-3-hexylthiophene 1 was added via a syringe, and the mixture was stirred at reflux for 1 h. The nickel catalyst, Ni(dppe)$_2$Cl$_2$ (2.25 mol%) was added in one portion. The mixture was stirred for 10 min at room temperature, and the Grignard reagent 3-[bis(trimethylsilyl)amino]phenyl magnesium chloride (5.0 mL, 10.0 mmol) was added via a syringe and the mixture was stirred at reflux for 1 h. The nickel catalyst, Ni(dppe)$_2$Cl$_2$ (2.25 mol%) was added in one portion. The mixture was stirred for 10 min at room temperature, and the Grignard reagent 3-[bis(trimethylsilyl)amino]phenyl magnesium chloride (5.0 mL, 10.0 mmol) was added via a syringe and the mixture was stirred at reflux for 1 h.

Initially, a ZnO seed layer (ca. 17 nm in thickness) was spin-coated on the pre-patterned indium tin oxide (ITO) coated glass from a 0.35 M solution of zinc acetate dehydrate (Riedel-de Haën) in the cosolvents of monoethanolamine (Merk) and 2-methoxyethanol (Acros) [30] at a rate of 3000 rpm. The film was then annealed at 200 °C for an hour to remove the residual organic solvents. The oriented ZnO-NR arrays were subsequently grown from the ZnO seed-coated substrates by using the hydrothermal method [31]. The resulting ZnO-NRs are ~120 nm in length with an average diameter and rod-to-rod distance of 30 nm and 20–40 nm, respectively.

The oriented ZnO-NR arrays were subsequently immersed in 1.3 $\times$ 10$^{-4}$ M O3HT-NH$_2$ anhydrous toluene solution at 60 °C for overnight followed by depositing the photoactive layer on top of the resulting structure. The active layer was formed by spin-coating the 40 mg mL$^{-1}$ solution of P3HT:PCBM at 1:0.8 weight ratio greatingichlorobenzene at a rate of 400 rpm. The thickness of the resulting films was ~200 nm. The solar cell was then completed by thermally depositing a silver layer (~100 nm) on top of the photoactive layer. Typical device active areas defined by the overlapping of ITO and silver electrodes are 4.0 mm$^2$.

The transmission electron microscopy (TEM) images were acquired on a FEI field-emission TEM, Tecnai F20, operated at 200 KV. The infrared spectra were determined at room temperature with a Perkin–Elmer Spectrum 1000 Fourier infrared spectroscopy (FTIR) system by a conventional method with a single cell. The luminescence (PL) spectroscopy was performed using a Jobin Yvon spec-1403 spectral system working in the double-grating mode. Kelvin probe force microscopy (KFM) measurements were performed in dark and under illumination of a halogen lamp (Royal Philips Electronics, 139, 50W) by Veeco Instruments Multimode AFM with an extended electronics module operating in the lift mode (typical lift height 20 nm) by a silicon cantilever with a PmIr surface coating. The charge extraction in linearly increasing voltage (CELIV) measurement was conducted in dark through a Tectronic Model AFG3101 function generator to generate input voltage ramp pulses and the response signals were recorded simultaneously from a load in series to the photovoltaic cell using an Aligent Model DSOS0504A oscilloscope. The current–voltage (J–V) characteristics of the finished solar cell devices were evaluated using a Keithley Model 2400 source meter under illumination intensity of 100 mW/cm$^2$ from a solar simulator (Newport Inc.) with AM 1.5 G filter. The incident photon-to-current conversion efficiency (IPCE) spectra were performed with a setup consisting of a lamp system, a chopper, a monochromator, a lock-in amplifier, and a standard silicon photodetector (ENLI Technology). All the characterizations were carried out in air at room temperature.

3. Results and discussion

Fig. 1(b) shows the TEM image of the adsorption of O3HT-NH$_2$ on ZnO-NRs surface. The dark contrast is the ZnO, which is revealed by the inset selected-area electron diffraction (SAED) pattern, indicating that the obtained ZnO-NR is monocristalline and wurtzite-type structure and oriented in c-axis direction; i.e., [0001] direction. A few nanometer thick O3HT-NH$_2$ layer covers the ZnO-NR surface as indicated by the arrows. The thickness of the adsorbed layer ranges from 1.5 to 5 nm (Fig. 1(c)), which may be due to the contour length distribution of O3HT-NH$_2$ molecule of an averaged MW of 3,438 KDa with a high PDI of 3.21. Apparently, the incubation of ZnO-NR arrays in O3HT-NH$_2$ solution results in a monolayer of O3HT-NH$_2$ absorbing on ZnO-NR surface instead of a film deposited on ZnO-NR arrays. Fig. 1(d) depicts the FTIR spectra taken from 500 to 3500 nm for ZnO-NR arrays before and after immersed in toluene-based O3HT-NH$_2$ solution. After immersion, the spectrum
shows no change of the transmission intensity except in the region of 2850–3000 nm (see Fig. 1(e)). There are three abrupt reduction bands around 2850, 2925, and 2963 nm. These are the typical CH stretching features, which can be attributed to the vibration of the methylene groups of the O3HT-NH₂ molecule [32,33]. The obtained alkyl side chain vibration characteristics suggest the adsorption of O3HT-NH₂ molecules on the ZnO-NR surface forming the ZnO-NR/O3HT-NH₂ structure.

The effect of O3HT-NH₂ adsorbed on ZnO-NR surface can be understood by photoluminescence (PL) spectroscopy. As seen in Fig. 2, the PL spectrum of pristine ZnO-NRs exhibits a sharp and a relatively broad luminescence peaks centered at 375 and 550 nm, respectively. The sharp and the broad peaks result from the band-to-band and defect band-to-band recombination of excited carriers in ZnO-NR arrays, respectively. These two categories of carrier relaxation routes display the comparable irradiation intensity. After a layer of O3HT-NH₂ adsorbing on ZnO-NR surface, the irradiation intensity of the former is stronger than that of the latter suggesting a reduction of surface defect concentration. The existence of O3HT-NH₂ on ZnO-NR surface can therefore effectively passivate the surface for lower surface defect status.

Since the incorporation of O3HT-NH₂ layer can reduce the surface defect density, we employ the Kelvin probe force microscopy (KFM) measurements [34–36] to gain more insight of the charge conduction influenced by the modification layer. We probe the relative surface potential (RSP) both in dark and under illumination for ZnO-NR/P3HT:PCBM and ZnO-NR/O3HT-NH₂/P3HT:PCBM structures on a 2 μm × 3 μm surface area. In a dark environment, both images are composed of brighter and darker domains, which correspond to the local Fermi level alignment of the P3HT-rich and PCBM-rich regions with the underneath ZnO-NR/ITO structure, respectively [37]. Particularly, the RSP distribution in dark for O3HT-NH₂-free structure is relatively
homogeneous (see Fig. 3(a)) while that for the modified one presents the scatter of large fiber-like brighter blocks (see Fig. 3 (b)). The obtained RSP across the measured surface area are 238–258 mV for the former and 510–530 mV for the latter.

Upon illumination, the photogenerated excitons diffuse in P3HT phase and dissociate at the P3HT(PCBM) or P3HT/ZnO-NR interfaces. Electrons migrate to the bottom ITO electrode through PCBM/ZnO-NR path and holes diffuse toward the top surface (anodic surface) through P3HT regions. The enhanced contrast within the KFM image reveals the final result of charge transport after exciton dissociation within the film. The measured RSPs for ZnO-NR/P3HT:PCBM and ZnO-NR/O3HT-NH2/P3HT:PCBM are 256–276 mV (Fig. 3(c)) and 604–624 mV (Fig. 3(d)), respectively. The RSPs for both structures shift positively as compared to the values in dark showing the accumulation of extra positive charges on the surface under illumination. The average shifts of RSP under illumination are 18 (before) and 94 meV (after). The relatively large positive shift of RSP after modification reveals an increase in hole concentration reaching the top surface to be extracted to the anode, a result supporting the reduced free carrier loss from being trapped or recombined at the ZnO-NRs due to the reduction of the surface defect states.

On the other hand, Zeng et al. [38] point out that the enhanced RSP correlates with the improvement in the surface charge density and its mobility. We deposited a silver layer on top of the polymer blend to complete the photovoltaic cells and those devices were used directly for mobility measurements. Fig. 4 presents the device mobility measurement results by employing the charge-extraction-from-the-linear-increasing-voltage (CELIV) method [39–42]. The input voltage ramp pulses were from –0.35 to 2 V over a period of 40 μs and the corresponding current responses for devices before and after O3HT-NH2 modification were recorded (see Fig. 4). Based on the recorded current transients, we calculated the individual carrier mobility (μ) by using

\[ \mu = \frac{2d^2}{\Delta \tau_{\text{max}}} \left[ 1 + 0.36 \Delta \tau(t) ](t) \right] \text{[40]}, \]

where \( d \), \( \Delta \tau_{\text{max}} \), \( \Delta \tau(t) \), and \( j(t) \) stand for the device thickness, time period required for maximum extraction current, the maximum extraction current \( (\Delta \tau(t) = \tau_{\text{max}}) \), and the capacitive displacement current \( (j(t) = 0) \), respectively. The device mobilities were estimated to be 9.7 × 10^-4 cm²/Vs (before) and 2.6 × 10^-4 cm²/V s (after).

In a BHJ system, CELIV technique probes the mobility of more mobile species or both if their values are comparable [43]. Baumann et al. [44] pointed out that the electron mobility

\( \approx 10^{-4} \text{ cm²/V s} \) is 10-fold higher than the hole mobility in the P3HT:PCBM blend. Thus, we assign the only carrier type detected here to be the electron. The hole mobility could be improved after O3HT-NH2 treatment, but the improvement is not large enough to have the same order of magnitude as electron to be detected in the measuring time window of the technique used. The incorporating of O3HT-NH2 molecule on ZnO-NR surface enhances the electron mobility by almost 3-fold.

The intermixing of the donor and acceptor materials forms a three-dimensional interpenetration network system. Electrons and holes travel in the respective network for conduction. The morphology of the network correlates with the transport property of the carrier and can be characterized by carrier mobility. Since there is a 3-fold enhancement in the electron mobility, the morphology of the electron conduction network is expected to be altered; hence, its counterpart, the hole conduction one, should respond accordingly. The change of BHJ morphology is also supported by the differences in RSP distribution features in dark as well as under light illumination. Several reports have shown that a BHJ system of more balanced charge transport properties [45–47] is important to reduce charge storage in the BHJ system. Unbalanced charge transport results in accumulation of slower charge species within the BHJ. Since larger hole concentration diffuse to the anodic surface for extraction, the nanomorphology
of the bi-carrier transport networks of the hybrid is thus modulated toward a more efficient charge transport configuration.

Based on the schematic solar cell configuration shown in the inset in Fig. 5(a), we evaluate and compare the device performance before and after the O3HT-NH$_2$ modification under one sun irradiation with AM 1.5 G filter and the obtained $J$–$V$ characteristics are shown in Fig. 5(a). The short circuit current ($J_{SC}$), open circuit voltage ($V_{OC}$), fill factor (FF), and PCE for device before modification are 6.0 mA/cm$^2$, 0.40 V, 0.42, and 1.28%, respectively, while those for the modified one are 8.8 mA/cm$^2$, 0.49 V, 0.40, and 1.73%, respectively. The presence of O3HT-NH$_2$ on the surface of ZnO-NR results in ~46% and ~22% increments in $J_{SC}$ and $V_{OC}$, respectively, while FF remains. Both the photocurrent and photovoltage improvement enhance the device performance up to 35%. Fig. 5(b) depicts the corresponding EQE spectra for both devices. The EQE values for the modified device enhance over the entire measured wavelength regime. As an example, an EQE value of 38.8% at a wavelength of 510 nm for the standard device increases to 47.7% after O3HT-NH$_2$ treatment. The difference of the underneath area reflects the additional extracted charges observed in $J_{SC}$ enhancement.

The improved device performance can be understood as follows. As described above, the O3HT-NH$_2$ layer reduces the defect density on the ZnO-NR surface, enhances carrier mobilities, and promotes the formation of a more efficient charge transport BHJ configuration such that the photo-generated free carriers can reach the respective electrodes for collection at their maximum capacity leading to $J_{SC}$ improvement. It was reported [48,49] that the large spatial dimension of the surface modifier can effectively block the back transfer of electrons to compensate holes on the polymer backbone resulting in a decrease in interfacial recombination events. The conductive oligomer of ~20 repeat units used in this study is considered as a large molecule for its naturally coil form and can have good blocking ability on back transfer recombination, which may account for the photocurrent enhancement as well. In addition to reduced surface trapped charges on ZnO-NR surface, the large enhancement of free carriers in the constituent phase enlarges the quasi-Fermi level separation leading to improved $V_{OC}$. Additionally, the O3HT-NH$_2$ molecules could possibly fill up or cover pinholes in the ZnO seed layer to prevent direct contact of P3HT from ITO electrode [20]. This pinhole blocking effect can contribute to $V_{OC}$ improvement as well.

The molecular weight of O3HT-NH$_2$ used has a large PDI of 3.21. We did not put special effort to synthesize the oligomer with low PDI. However, the PDI of the oligomer can be reduced by solvent extraction. Usually, the lower molecular weight conjugated oligomer exhibits lower conductivity. With a high PDI oligomer, the conductivity of the oligomer will be limited by the lower molecular weight molecule in the oligomer. However, in our study, the oligomer with a PDI of 3.21 serves as the purpose to reduce the recombination of electron and hole and to facilitate the charge transport. We have also tried to use O3HT-NH$_2$ of higher molecular weight (MW ~5.6 KDa) to modify the solar cell and the resulting device does not perform as well as the one modified by the lower MW. The dependency of solar cell performance on the MW of the surface modifier is worth of further study, and is among our ongoing research.

We stress here that the surface modifier used in this study is a metal-free conjugated oligomer of relatively lower cost as compared to the metal-containing conductive compound reported in the literature. Our selection of surface modifier improves the compatibility between the inorganic metal oxide and the organic blend leading to an apparent modulation in the microscopic mixing result of the polymer blend. The bi-carrier transport pathways become more ordered and are of greater carrier transport efficiency. The finding provides a least expensive and useful alternative to overcome the organic–inorganic interfacial problems.

4. Summary

We synthesize a metal-free conductive oligomer composed of a short segment structure of the light-harvesting polymer to adsorb on the ZnO-NR surface. This conjugated oligomer passivates the ZnO-NR surface for its adsorption activity. In addition, in the presence of this oligomer layer, the contacting BHJ blend with its microscopic morphology resulting from dual substance mixing is altered as suggested by the improved charge transport properties and the different features of KFM images. The nanomorphology manipulation effect induced by the metal-free conjugated surface modifier is also a major factor for the performance improvement of the photovoltaic cells. Our result shown here therefore provides an excellent key step for the application of hybrid organic–inorganic solar cells.

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